

H5N2509P

Silicon N Channel MOS FET High Speed Power Switching

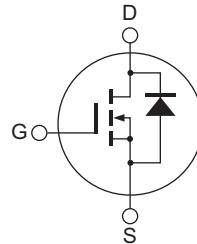
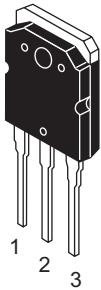
REJ03G1109-0200
(Previous: ADE-208-1378)
Rev.2.00
Sep 07, 2005

Features

- Low on-resistance: $R_{DS(on)} = 0.053 \Omega$ typ.
- Low leakage current: $I_{DSS} = 1 \mu\text{A}$ max (at $V_{DS} = 250 \text{ V}$, $V_{GS} = 0 \text{ V}$)
- High speed switching: $t_f = 110 \text{ ns}$ typ (at $I_D = 15 \text{ A}$, $R_L = 8.3 \Omega$, $V_{GS} = 10 \text{ V}$)
- Low gate charge: $Q_g = 110 \text{ nC}$ typ (at $V_{DD} = 200 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 30 \text{ A}$)
- Avalanche ratings

Outline

RENESAS Package code: PRSS0004ZE-A
(Package name: TO-3P)



1. Gate
2. Drain (Flange)
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	30	A
Drain peak current	I _D (pulse) ^{Note 1}	120	A
Body-drain diode reverse drain current	I _{DR}	30	A
Body-drain diode reverse drain peak current	I _{DR} (pulse) ^{Note 1}	120	A
Avalanche current	I _{AP} ^{Note 3}	30	A
Channel dissipation	P _{ch} ^{Note 2}	150	W
Channel to case thermal Impedance	θ _{ch-c}	0.833	°C/W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

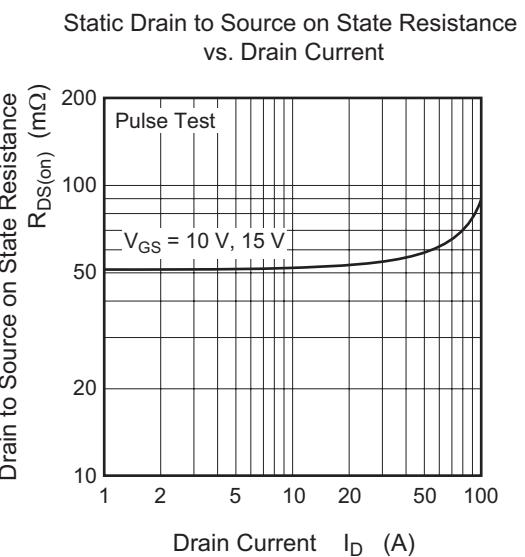
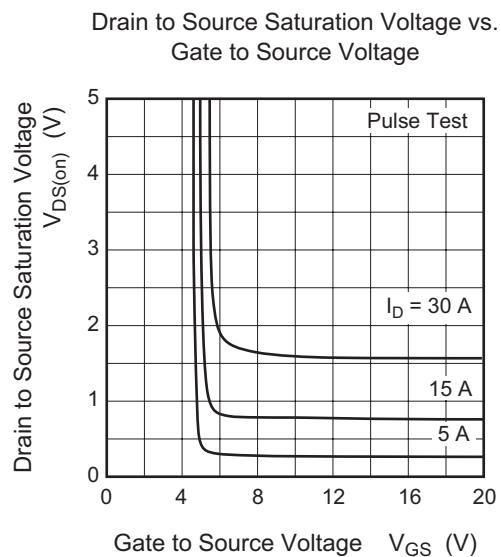
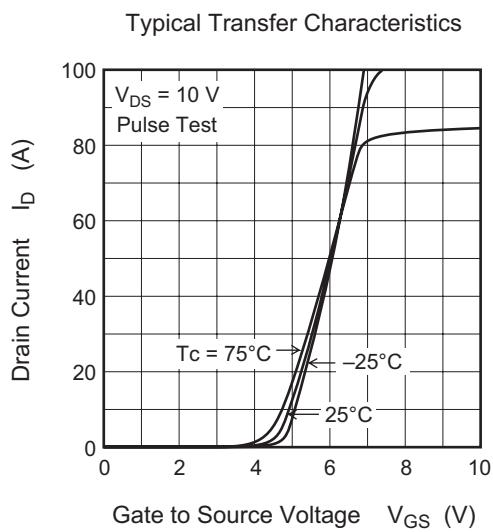
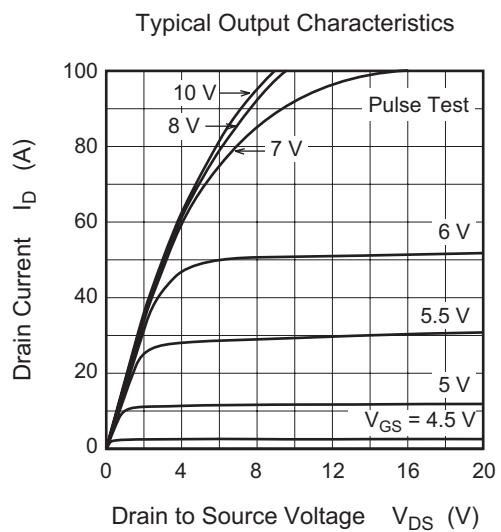
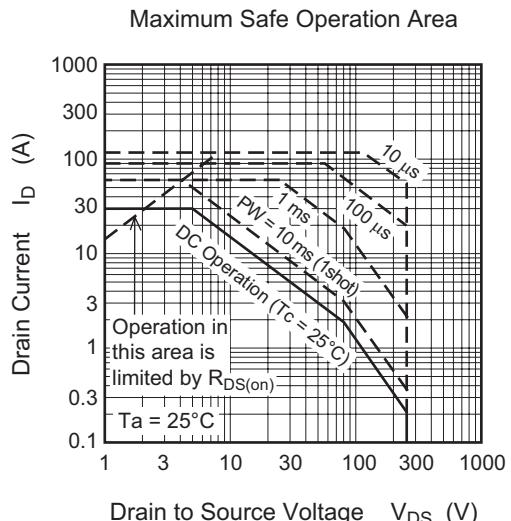
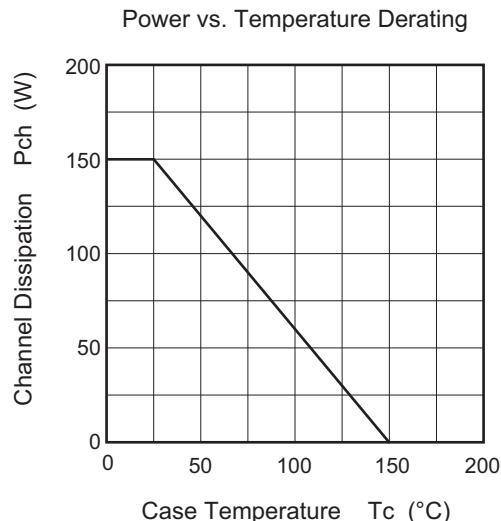
2. Value at T_c = 25°C3. T_{ch} ≤ 150°C**Electrical Characteristics**

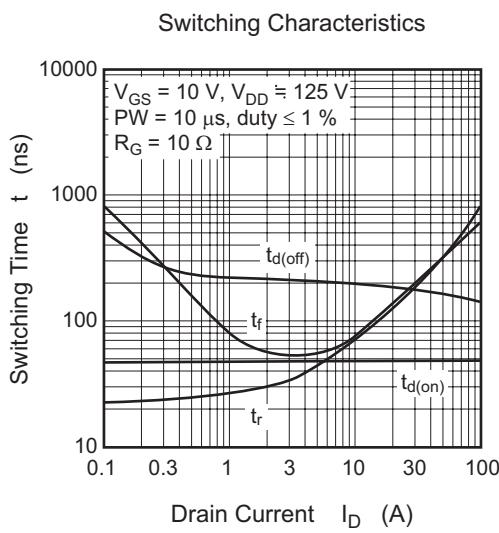
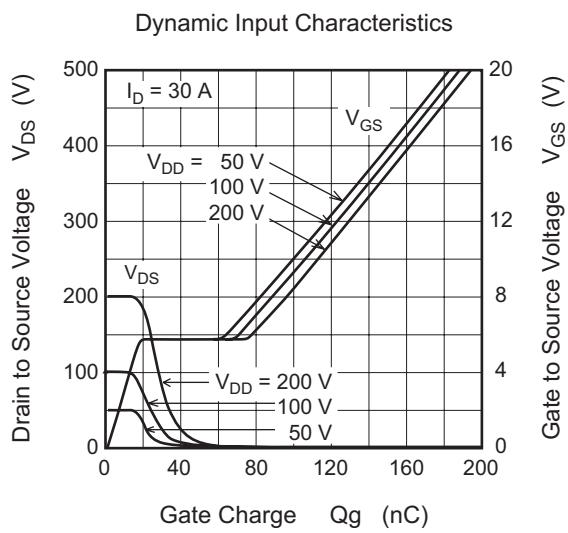
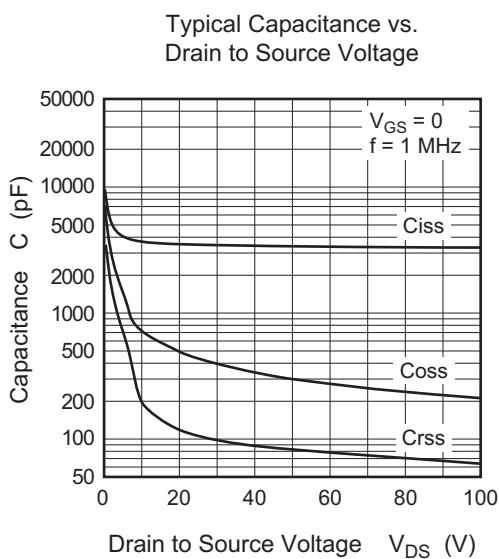
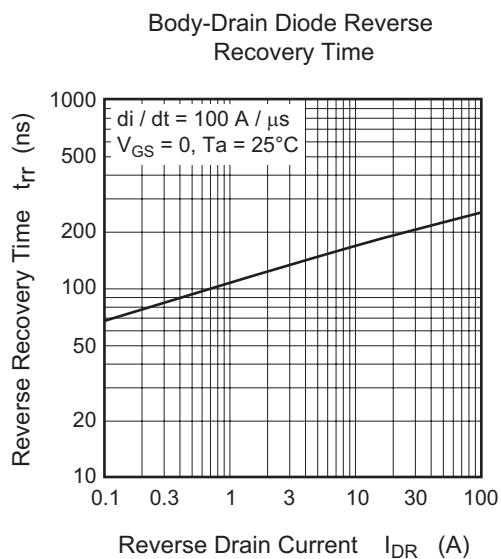
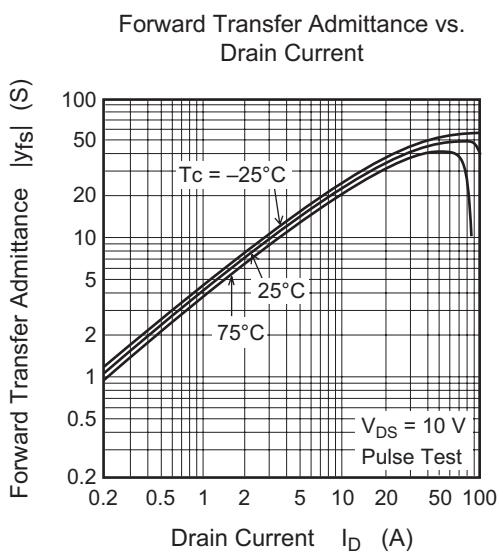
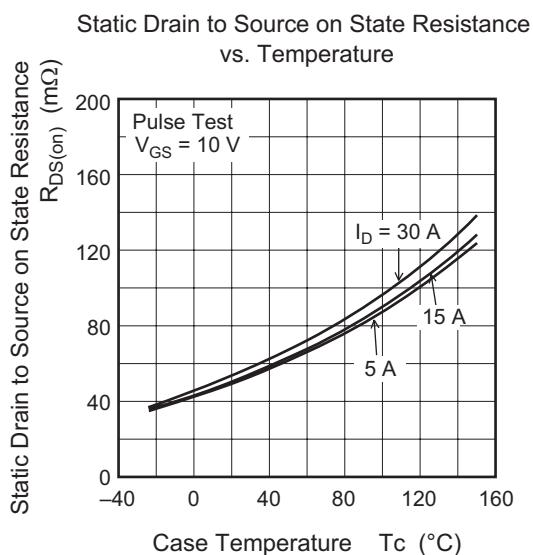
(Ta = 25°C)

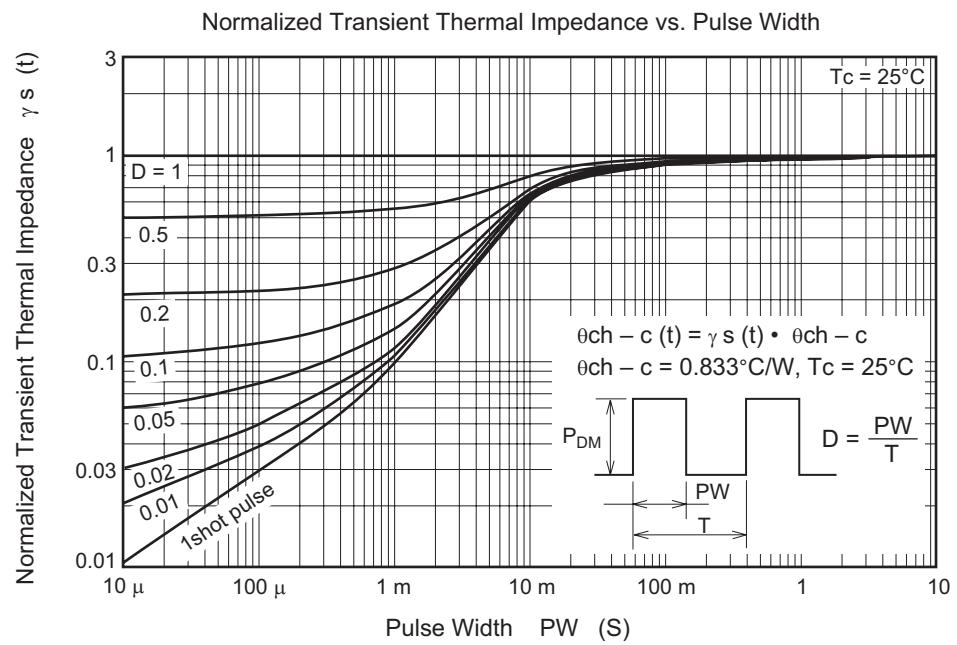
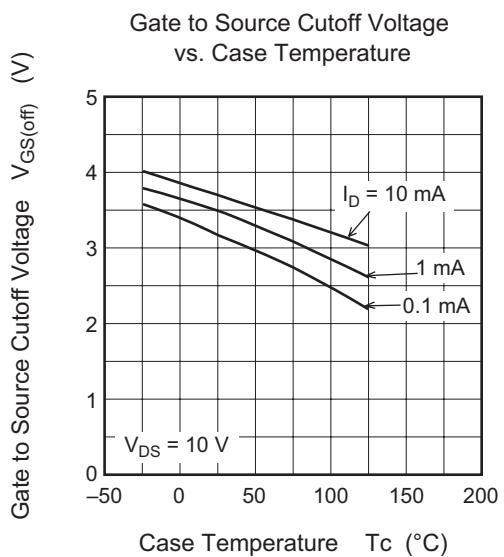
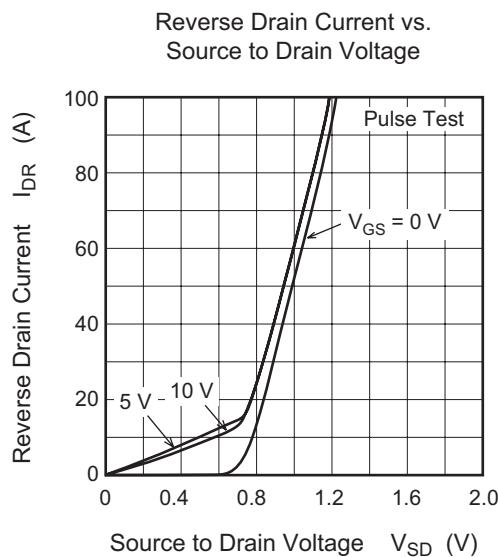
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	250	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±0.1	μA	V _{GS} = ±30 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} = 250 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	3.0	—	4.0	V	V _{DS} = 10 V, I _D = 1 mA
Static drain to source on state resistance	R _{DS (on)}	—	0.053	0.069	Ω	I _D = 15 A, V _{GS} = 10 V ^{Note 4}
Forward transfer admittance	Y _{fs}	17	28	—	S	I _D = 15 A, V _{DS} = 10 V ^{Note 4}
Input capacitance	C _{iss}	—	3600	—	pF	V _{DS} = 25 V
Output capacitance	C _{oss}	—	450	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	115	—	pF	f = 1 MHz
Turn-on delay time	t _{d (on)}	—	48	—	ns	I _D = 15 A
Rise time	t _r	—	120	—	ns	V _{GS} = 10 V
Turn-off delay time	t _{d (off)}	—	190	—	ns	R _L = 8.3 Ω
Fall time	t _f	—	110	—	ns	R _g = 10 Ω
Total gate charge	Q _g	—	110	—	nC	V _{DD} = 200 V
Gate to source charge	Q _{gs}	—	19	—	nC	V _{GS} = 10 V
Gate to drain charge	Q _{gd}	—	53	—	nC	I _D = 30 A
Body-drain diode forward voltage	V _{DF}	—	0.9	1.35	V	I _F = 30 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	—	210	—	ns	I _F = 30 A, V _{GS} = 0
Body-drain diode reverse recovery charge	Q _{rr}	—	1.8	—	μC	di _F /dt = 100 A/μs

Note: 4. Pulse test

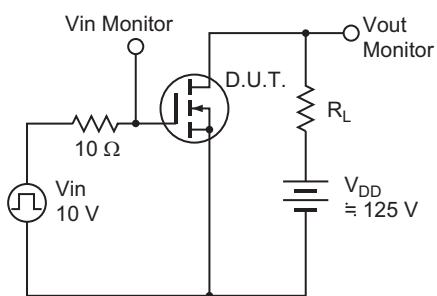
Main Characteristics



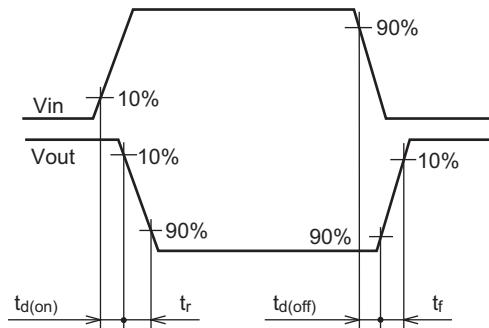




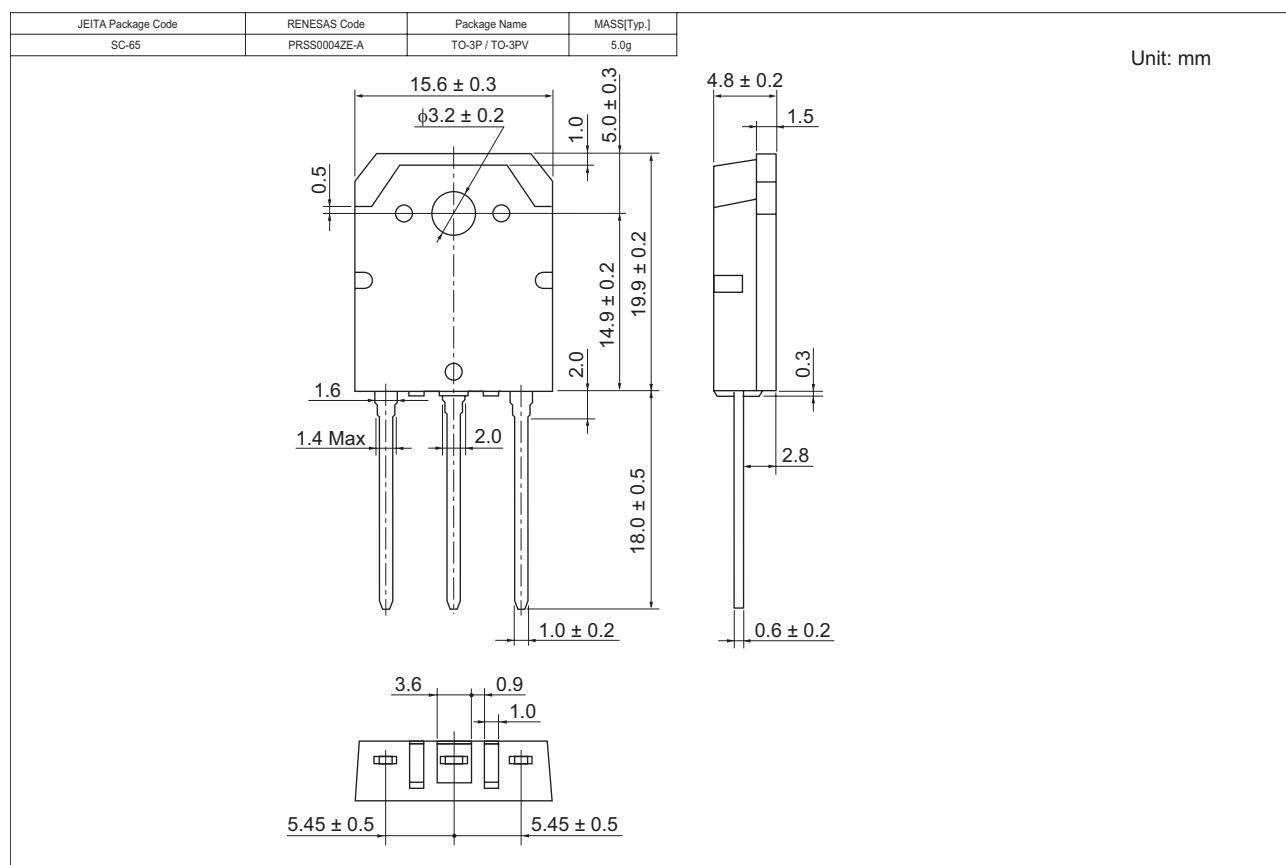
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N2509P-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
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Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
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Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510